March 2000

FDN5630

FDN5630

60V N-Channel PowerTrench® MOSFET

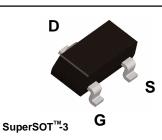
General Description

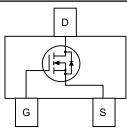
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

This MOSFET features very low R_{DS(ON)} in a small SOT23 footprint. Fairchild's PowerTrench technology provides faster switching than other MOSFETs with comparable R_{DS(ON)} specifications. The result is higher overall efficiency with less board space.

Applications

- DC/DC converter
- Motor drives





• 1.7 A, 60 V. $R_{DS(ON)} = 0.100 \Omega @ V_{GS} = 10 V$

 $R_{DS(ON)} = 0.120 \ \Omega \ @ V_{GS} = 6 \ V.$

• Optimized for use in high frequency DC/DC converters.

SuperSOT[™] - 3 provides low R_{DS(ON)} in SOT23 footprint.

Absolute Maximum Ratings T_A = 25 C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		60	V
V _{GSS}	Gate-Source Voltage		±20	V
ID	Drain Current - Continuous	(Note 1a)	1.7	A
	- Pulsed		10	
PD	Power Dissipation for Single Operation	(Note 1a)	0.5	W
		(Note 1b)	0.46	
TJ, T _{stg}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Features

• Low gate charge.

· Very fast switching.

Thermal Characteristics

R _e JA	Thermal Resistance, Junction-to-Ambient	(Note 1a)	250	°C/W
R _⊕ JC	Thermal Resistance, Junction-to-Case	(Note 1)	75	°C/W

Package Marking and Ordering Information

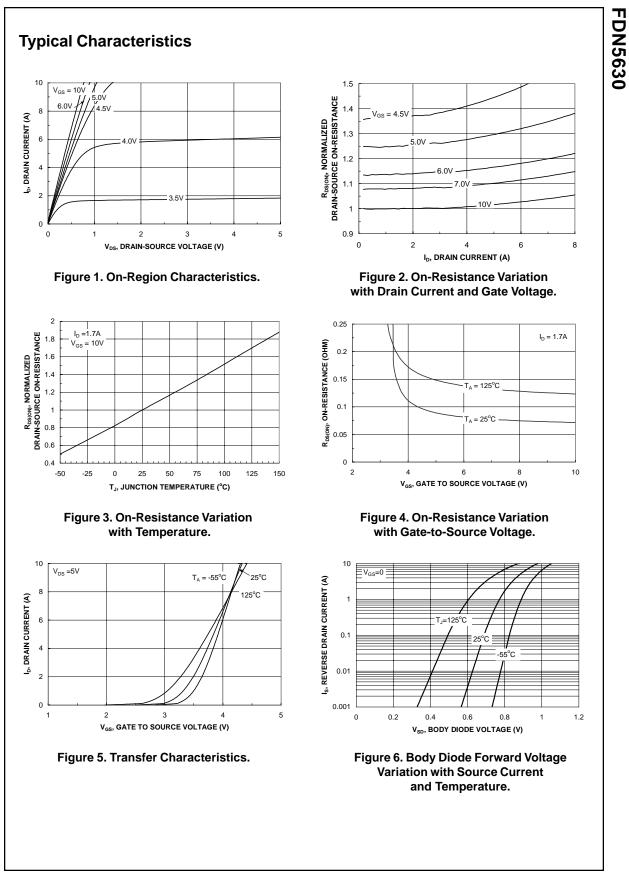
Device Marking	Device	Reel Size	Tape Width	Quantity
5630	FDN5630	7	8mm	3000 units

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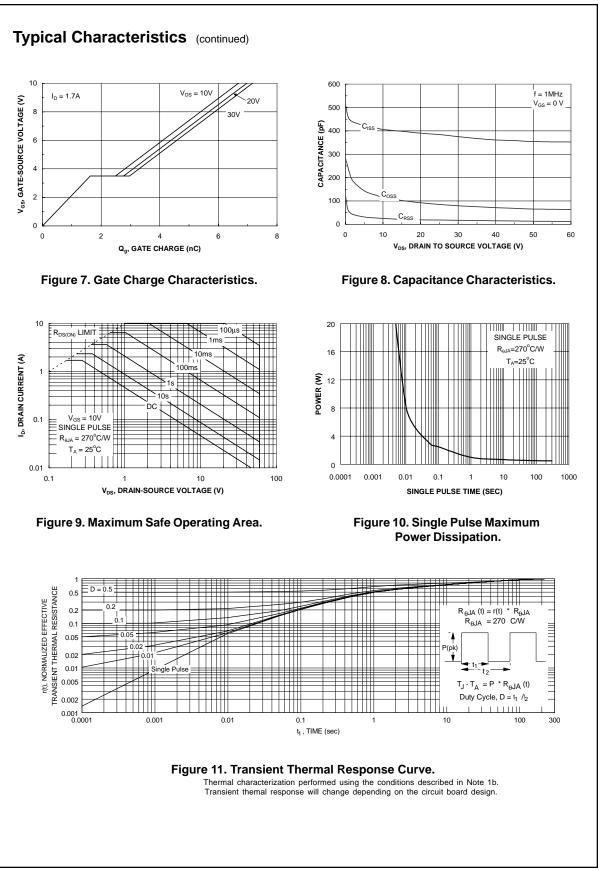
Incteristics Drain-Source Breakdown Voltage Breakdown Voltage Temperature					
Drain-Source Breakdown Voltage Breakdown Voltage Temperature	1				
	$V_{GS} = 0 V, I_D = 250 \mu A$	60			V
Coefficient	I_D = 250 µA,Referenced to 25°C		63		mV/°
Zero Gate Voltage Drain Current	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA
Gate-Body Leakage Current, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
Gate-Body Leakage Current, Reverse	$V_{GS} = -20 V, V_{DS} = 0 V$			-100	nA
ICTERISTICS (Note 2)					
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$	1	2.4	3	V
Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}, \text{Referenced to } 25^\circ\text{C}$		6.9		mV/°
Static Drain-Source On-Resistance	$V_{GS} = 10 V, I_D = 1.7 A$ $V_{GS} = 10 V, I_D = 1.7 A, T_J = 125^{\circ}C$ $V_{GS} = 6 V, I_D = 1.6 A$		0.073 0.127 0.083	0.100 0.180 0.120	Ω
On-State Drain Current	$V_{GS} = 10 \text{ V}, \text{ V}_{DS} = 1.7 \text{ V}$	5			A
Forward Transconductance	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1.7 \text{ A}$		6		S
Characteristics					
	$V_{DS} = 15 \text{ V}, \text{ V}_{GS} = 0 \text{ V},$	1	400		pF
Output Capacitance	f = 1.0 MHz		102		pF
Reverse Transfer Capacitance	-		21		pF
Characteristics	-				
	$V_{DD} = 30 V_{c} I_{D} = 1 A_{c}$		10	20	ns
	$V_{GS} = 10 \text{ V}, \text{ R}_{GEN} = 6 \Omega$		6		ns
	-		15	28	ns
Turn-Off Fall Time	-		5	15	ns
Total Gate Charge	V _{DS} = 20 V, I _D = 1.7 A,		7	10	nC
Gate-Source Charge	V _{GS} = 10 V,		1.6		nC
Gate-Drain Charge	-		1.2		nC
mee Diede Chevesteristics			1		
			1	0.42	A
Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, \text{ I}_{S} = 0.42 \text{ A} (\text{Note 2})$		0.72	1.2	V
	Forward Gate-Body Leakage Current, Reverse Cteristics (Note 2) Gate Threshold Voltage Temperature Coefficient Static Drain-Source On-Resistance On-State Drain Current Forward Transconductance Characteristics Input Capacitance Output Capacitance Output Capacitance Potaracteristics (Note 2) Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Total Gate Charge Gate-Source Charge Gate-Drain Charge Image: Surger Characteristics and Charact	ForwardVGate-Body Leakage Current, ReverseVGS = -20 V, VDS = 0 VGate-Body Leakage Current, ReverseVGS = -20 V, VDS = 0 VGate Threshold VoltageVDS = VGS, ID = 250 μ AGate Threshold VoltageID = 250 μ A, Referenced to 25°CGate Threshold VoltageVGS = 10 V, ID = 1.7 ATemperature CoefficientVGS = 10 V, ID = 1.7 A, TJ = 125°CStatic Drain-SourceVGS = 10 V, ID = 1.7 A, TJ = 125°COn-ResistanceVGS = 10 V, VDS = 1.7 VForward TransconductanceVDS = 10 V, VDS = 1.7 VForward TransconductanceVDS = 10 V, ID = 1.7 ACharacteristicsVDS = 15 V, VGS = 0 V, f = 1.0 MHzInput CapacitanceVDS = 15 V, VGS = 0 V, f = 1.0 MHzCharacteristics (Note 2)Turn-On Delay TimeTurn-On Rise TimeVDD = 30 V, ID = 1 A, VGS = 10 V, RGEN = 6 \OmegaTurn-Off Delay TimeVDS = 20 V, ID = 1.7 A, VGS = 10 V, Gate-Drain ChargeTotal Gate ChargeVDS = 20 V, ID = 1.7 A, VGS = 10 V, Gas = 10 V, Gas = 10 V,Turn-Off Fall TimeVDS = 20 V, ID = 1.7 A, VGS = 10 V, Gas = 10 V,Turn-Off Delay TimeVDS = 20 V, ID = 1.7 A, VGS = 10 V, Gas = 10 V,Turn-Off Fall TimeVDS = 20 V, ID = 1.7 A, VGS = 10 V, Gas = 10 V,Turn-Off Delay TimeVDS = 20 V, ID = 1.7 A, VGS = 10 V,Turn-Off Characteristics and Maximum RatingsMaximum Continuous Drain-Source Diode Forward Current	ForwardImage: Constraint of the second state of the second s	ForwardCVGSForwardGate-Body Leakage Current, ReverseVGS = -20 V, VDS = 0 VGate Threshold VoltageVDS = VGS, ID = 250 μ A12.4Gate Threshold VoltageID = 250 μ A, Referenced to 25°C6.9Temperature CoefficientID = 250 μ A, Referenced to 25°C6.9Static Drain-SourceVGS = 10 V, ID = 1.7 A0.073On-ResistanceVGS = 10 V, ID = 1.7 A, TJ = 125°C0.083On-State Drain CurrentVGS = 10 V, VDS = 1.7 V5Forward TransconductanceVDS = 10 V, ID = 1.7 A6CharacteristicsVDS = 15 V, VGS = 0 V, f = 1.0 MHz400Output CapacitanceVDS = 15 V, VGS = 0 V, f = 1.0 MHz102Input CapacitanceVDS = 15 V, VGS = 0 V, f = 1.0 MHz102Characteristics (Note 2)VDD = 30 V, ID = 1 A, VGS = 10 V, RGEN = 6 Ω 6Turn-On Delay Time Turn-Onff Fall TimeVDS = 20 V, ID = 1.7 A, VGS = 10 V, Gate-Source Charge7VGS = 10 V, RGEN = 6 Ω 15Total Gate Charge Gate-Drain ChargeVDS = 20 V, ID = 1.7 A, VGS = 10 V,7Ince Diode Characteristics and Maximum Ratings1.2Maximum Continuous Drain-Source Diode Forward Current1	ForwardConstrainedVoid of the term of term

FDN5630 Rev. C

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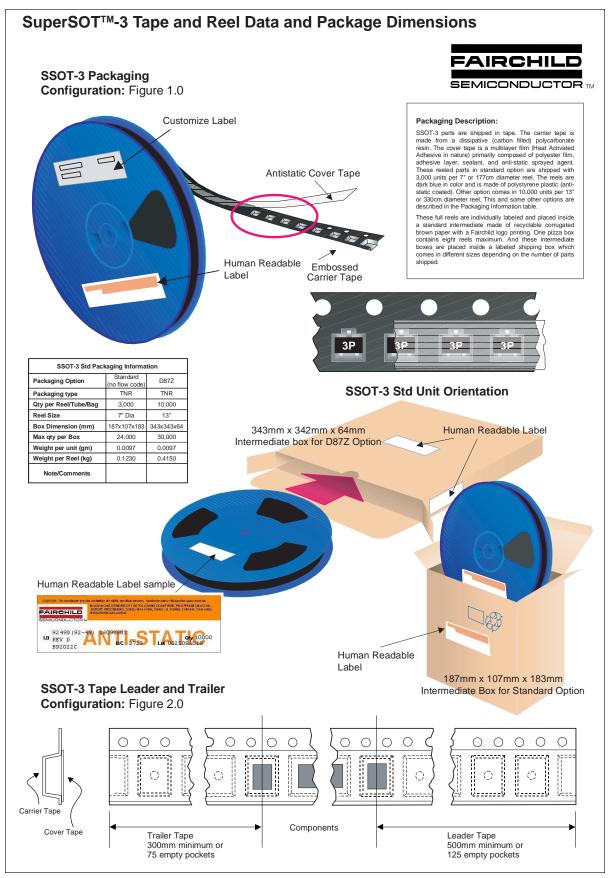


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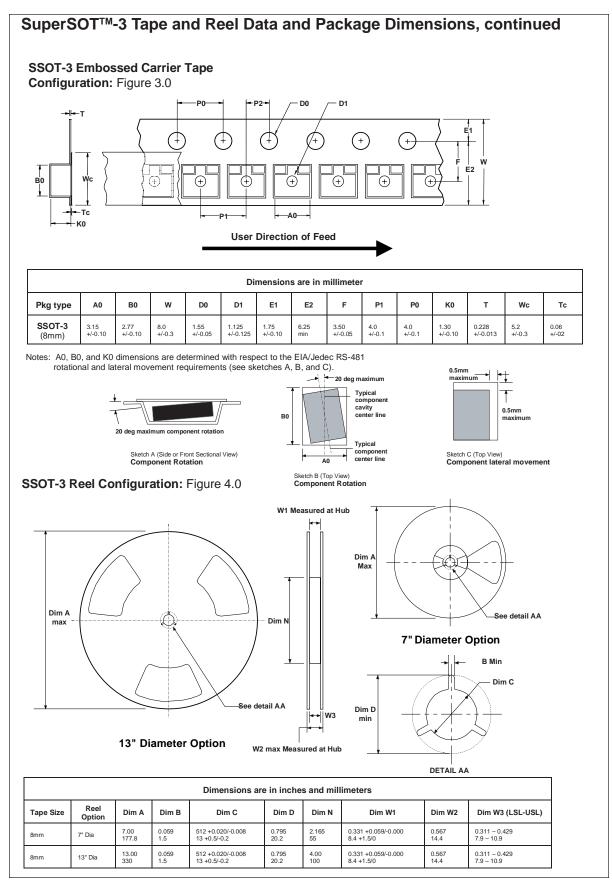


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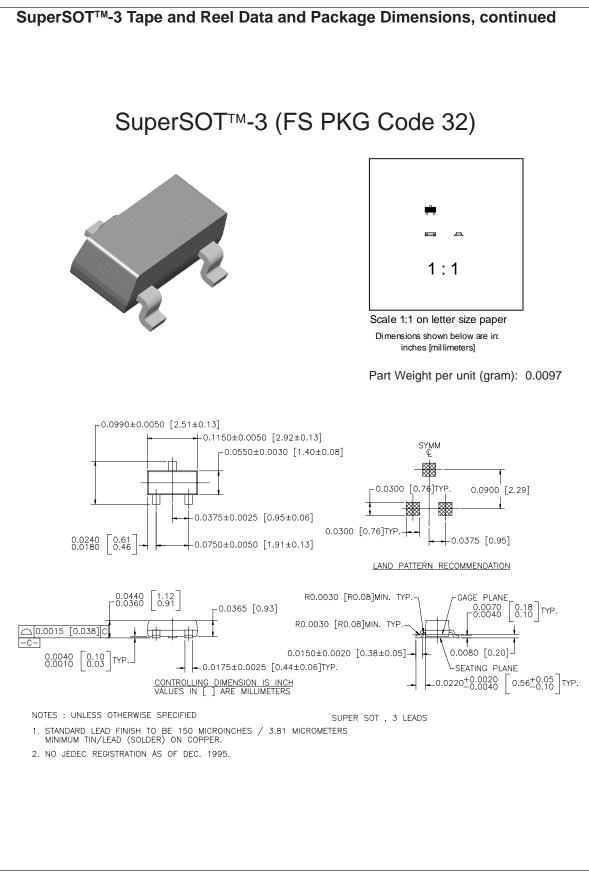
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August 1999, Rev. C



July 1999, Rev. C



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